



DMN6069SFG

60V N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D Max T _C = +25°C |
|-------------------|------------------------------|--|
| 60V | $50m\Omega$ @ $V_{GS} = 10V$ | 18A |
| 60 V | $63m\Omega @ V_{GS} = 4.5V$ | 16A |

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

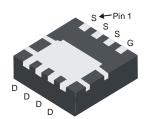
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products (PowerDI[®])
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (\$\sqrt{2}\$)
- Weight: 0.03 grams (Approximate)

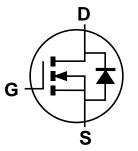


Bottom View



PowerDI3333-8

Top View



Equivalent Circuit

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---------------|---------------|-------------------|
| DMN6069SFG-7 | PowerDI3333-8 | 2,000/Tape & Reel |
| DMN6069SFG-13 | PowerDI3333-8 | 3,000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N69 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 16 = 2016) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Units |
|---|--------------|----------------------------------|-----------------|------------|-------|
| Drain-Source Voltage | | | V_{DSS} | 60 | V |
| Gate-Source Voltage | | | V_{GSS} | ±20 | V |
| Continuous Prain Current (Note 6) \/ 40\/ | Steady State | $T_A = +25$ °C $T_A = +70$ °C | I _D | 5.6 4.5 | А |
| Continuous Drain Current (Note 6) V _{GS} = 10V | Steady State | $T_C = +25$ °C $T_C = +70$ °C | I _D | 18 14.5 | А |
| Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%) | | | I _{DM} | 25 | Α |
| Maximum Continuous Body Diode Forward Current (Note 6) | | | I _S | 2.5 | Α |
| Avalanche Current (Note 7) L = 0.1mH | | | I _{AS} | 12 | Α |
| Avalanche Energy (Note 7) L = 0.1mH | | | E _{AS} | 7.2 | mJ |

Thermal Characteristics

| Characteristic | | Symbol | Value | Units |
|--|----------------|------------------|-------------|-------|
| Total Power Dissipation (Note 5) | | P_{D} | 0.93 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | C | 134 | °C/W |
| Thermal Resistance, Junction to Ambient (Note 5) | t<10s | $R_{\theta JA}$ | 82 | |
| Total Power Dissipation (Note 6) | | P_{D} | 2.4 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | D | 53 | °C/W |
| Themal Resistance, Junction to Ambient (Note 6) | t<10s | $R_{\theta JA}$ | 33 | |
| Thermal Resistance, Junction to Case | $R_{	heta JC}$ | 5 | | |
| Operating and Storage Temperature Range | | $T_{J,} T_{STG}$ | -55 to +150 | °C |

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|---------------------|-----|-----|-------|-------|---|--|
| OFF CHARACTERISTICS (Note 8) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 60 | _ | _ | V | $V_{GS} = 0V$, $I_D = 250\mu A$ | |
| Zero Gate Voltage Drain Current T _J = +25°C | I _{DSS} | | _ | 1 | μΑ | $V_{DS} = 60V$, $V_{GS} = 0V$ | |
| Zero Gate Voltage Drain Current T _J = +150°C (Note 9) | I _{DSS} | _ | _ | 100 | μΑ | $V_{DS} = 60V$, $V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | | _ | ±100 | nΑ | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 8) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 1 | _ | 3 | V | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | |
| Static Drain-Source On-Resistance | | _ | 39 | 50 | mΩ | $V_{GS} = 10V, I_D = 4.5A$ | |
| Static Brain Godice on Resistance | R _{DS(ON)} | _ | 47 | 63 | 11122 | $V_{GS} = 4.5V, I_D = 3A$ | |
| Diode Forward Voltage | V_{SD} | _ | _ | 1.1 | V | $V_{GS} = 0V, I_S = 2.5A$ | |
| On State Drain Current (Note 9) | I _{D(ON)} | 20 | _ | _ | Α | $V_{DS} \ge 5V$, $V_{GS} = 10V$ | |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | | |
| Input Capacitance | CISS | | 740 | 1,480 | pF | ., | |
| Output Capacitance | Coss | 1 | 40 | 80 | pF | $V_{DS} = 30V, V_{GS} = 0V,$ -f = 1.0MHz | |
| Reverse Transfer Capacitance | C _{RSS} | | 28 | 55 | pF | 1 = 1.000112 | |
| Gate Resistance | R_{G} | _ | 2.2 | 4 | Ω | $V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$ | |
| Total Gate Charge (V _{GS} = 4.5V) | Q_{G} | l | 6.4 | 12 | nC | | |
| Total Gate Charge (V _{GS} = 10V) | Q_{G} | | 14 | 25 | nC | V _{DS} = 30V. I _D = 12A | |
| Gate-Source Charge | Q _{GS} | 1 | 2.8 | 5.5 | nC | VDS = 30V, ID = 12A | |
| Gate-Drain Charge | Q_{GD} | | 2.3 | 5 | nC | | |
| Turn-On Delay Time | t _{D(ON)} | | 3.6 | 10 | ns | | |
| Turn-On Rise Time | t _R | | 5.0 | 10 | ns | $V_{DS} = 30V, I_D = 12A$ | |
| Turn-Off Delay Time | t _{D(OFF)} | _ | 12 | 24 | ns | $V_{GS} = 10V, R_G = 6.0\Omega$ | |
| Turn-Off Fall Time | t _F | _ | 3.3 | 10 | ns | | |
| Body Diode Reverse Recovery Time | t _{RR} | | 11 | 22 | ns | 1 454 4/4 4004/ | |
| Body Diode Reverse Recovery Charge | Q_{RR} | _ | 5.1 | 10 | nC | I _F = 4.5A, di/dt = 100A/μs | |

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

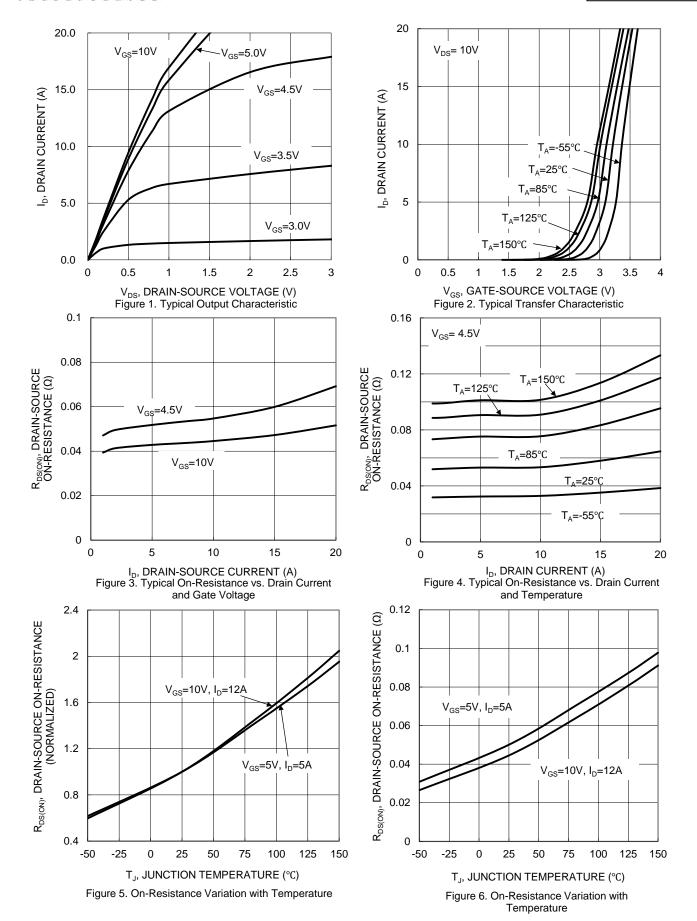
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

^{7.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_{J} = +25°C.

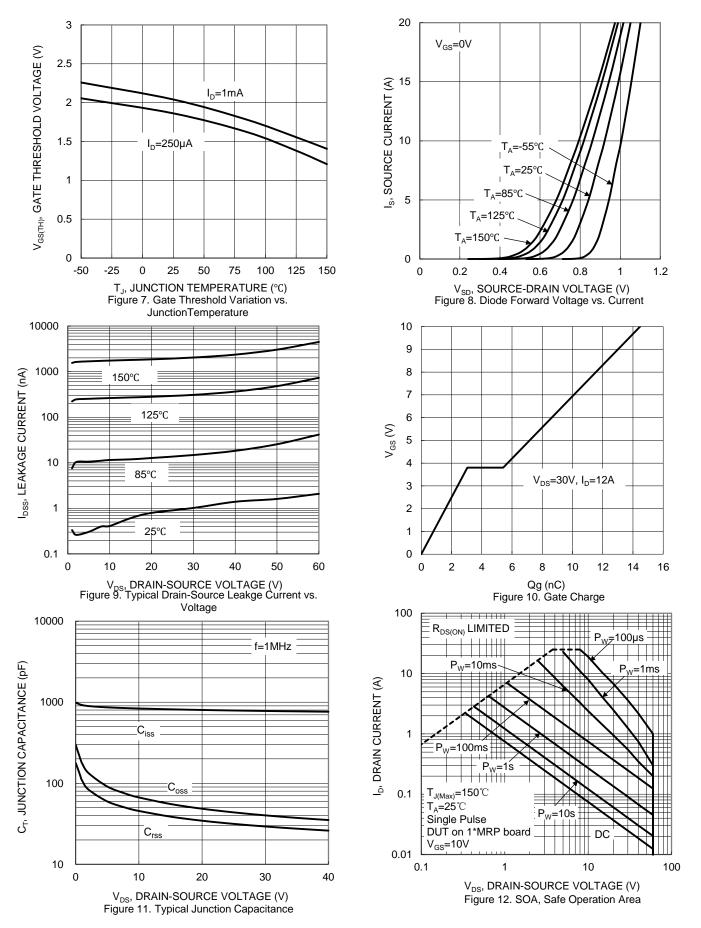
^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.

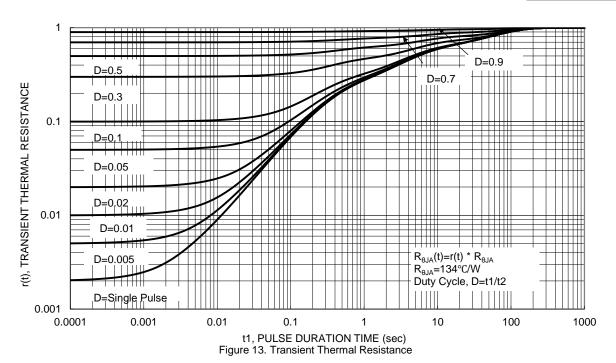










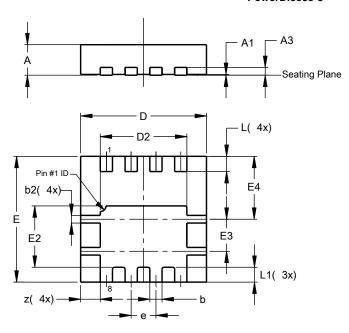




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

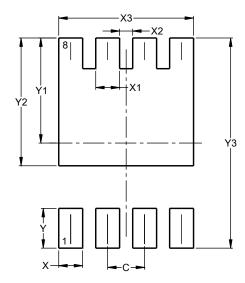


| PowerDI3333-8 | | | | | |
|----------------------|------|------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 0.75 | 0.85 | 0.80 | | |
| A1 | 0.00 | 0.05 | 0.02 | | |
| A3 | - | - | 0.203 | | |
| b | 0.27 | 0.37 | 0.32 | | |
| b2 | 0.15 | 0.25 | 0.20 | | |
| D | 3.25 | 3.35 | 3.30 | | |
| D2 | 2.22 | 2.32 | 2.27 | | |
| Е | 3.25 | 3.35 | 3.30 | | |
| E2 | 1.56 | 1.66 | 1.61 | | |
| E3 | 0.79 | 0.89 | 0.84 | | |
| E4 | 1.60 | 1.70 | 1.65 | | |
| е | _ | _ | 0.65 | | |
| L | 0.35 | 0.45 | 0.40 | | |
| L1 | _ | _ | 0.39 | | |
| Z | _ | _ | 0.515 | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



| Dimensions | Value (in mm) | | |
|------------|---------------|--|--|
| С | 0.650 | | |
| X | 0.420 | | |
| X1 | 0.420 | | |
| X2 | 0.230 | | |
| Х3 | 2.370 | | |
| Y | 0.700 | | |
| Y1 | 1.850 | | |
| Y2 | 2.250 | | |
| Y3 | 3.700 | | |



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